

0.9V Drive Nch + Nch MOSFET

EM6K34

● Structure

Silicon N-channel MOSFET

● Features

- 1) High speed switing.
- 2) Small package(EMT6).
- 3) Ultra low voltage drive(0.9V drive).

● Application

Switching

● Packaging specifications

Type	Package	Taping
	Code	T2R
	Basic ordering unit (pieces)	8000
EM6K34		○

● Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

<It is the same ratings for Tr1 and Tr2.>

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	50	V
Gate-source voltage		V_{GSS}	± 8	V
Drain current	Continuous	I_D	± 200	mA
	Pulsed	I_{DP}^{*1}	± 800	mA
Source current (Body Diode)	Continuous	I_S	125	mA
	Pulsed	I_{SP}^{*1}	800	mA
Power dissipation		P_D^{*2}	150	mW / TOTAL
			120	mW / ELEMENT
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Range of storage temperature		T_{stg}	-55 to +150	$^\circ\text{C}$

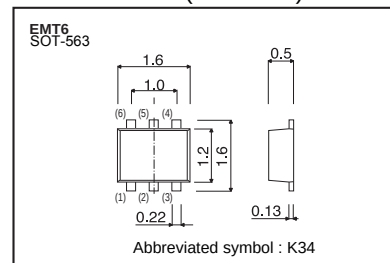
 $*1 P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$
 $*2$ Each terminal mounted on a recommended land.

● Thermal resistance

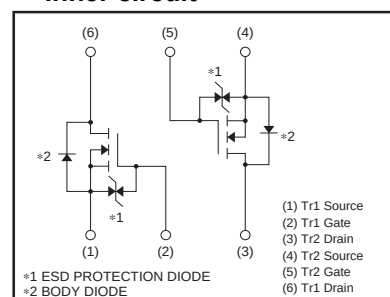
Parameter	Symbol	Limits	Unit
Channel to Ambient	$R_{th}(ch-a)^*$	833	$^\circ\text{C}/\text{W}/\text{TOTAL}$
		1042	$^\circ\text{C}/\text{W}/\text{ELEMENT}$

 $*$ Each terminal mounted on a recommended land.

● Dimensions (Unit : mm)



● Inner circuit



● **Electrical characteristics** ($T_a = 25^\circ\text{C}$)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 8\text{V}$, $V_{DS} = 0\text{V}$
Drain-source breakdown voltage	$V_{(BR)DSS}$	50	-	-	V	$I_D = 1\text{mA}$, $V_{GS} = 0\text{V}$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS} = 50\text{V}$, $V_{GS} = 0\text{V}$
Gate threshold voltage	$V_{GS(th)}$	0.3	-	0.8	V	$V_{DS} = 10\text{V}$, $I_D = 1\text{mA}$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	1.6	2.2	Ω	$I_D = 200\text{mA}$, $V_{GS} = 4.5\text{V}$
		-	1.7	2.4		$I_D = 200\text{mA}$, $V_{GS} = 2.5\text{V}$
		-	2.0	2.8		$I_D = 200\text{mA}$, $V_{GS} = 1.5\text{V}$
		-	2.2	3.3		$I_D = 100\text{mA}$, $V_{GS} = 1.2\text{V}$
		-	3.0	9.0		$I_D = 10\text{mA}$, $V_{GS} = 0.9\text{V}$
Forward transfer admittance	$ Y_{fs} ^*$	0.2	-	-	S	$I_D = 200\text{mA}$, $V_{DS} = 10\text{V}$
Input capacitance	C_{iss}	-	26	-	pF	$V_{DS} = 10\text{V}$
Output capacitance	C_{oss}	-	6	-	pF	$V_{GS} = 0\text{V}$
Reverse transfer capacitance	C_{rss}	-	3	-	pF	$f = 1\text{MHz}$
Turn-on delay time	$t_{d(on)}^*$	-	5	-	ns	$I_D = 100\text{mA}$, $V_{DD} \approx 25\text{V}$
Rise time	t_r^*	-	8	-	ns	$V_{GS} = 4.5\text{V}$
Turn-off delay time	$t_{d(off)}^*$	-	17	-	ns	$R_L = 250\Omega$
Fall time	t_f^*	-	43	-	ns	$R_G = 10\Omega$

*Pulsed

● **Body diode characteristics** (Source-Drain) ($T_a = 25^\circ\text{C}$)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	1.2	V	$I_S = 200\text{mA}$, $V_{GS} = 0\text{V}$

*Pulsed

● Electrical characteristics curves

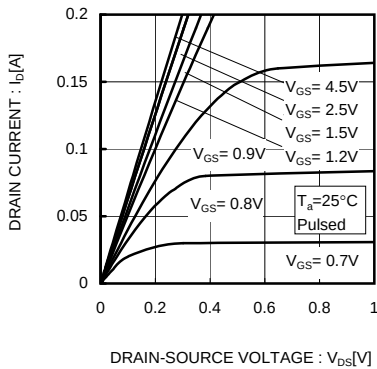


Fig.1 Typical Output Characteristics(I)

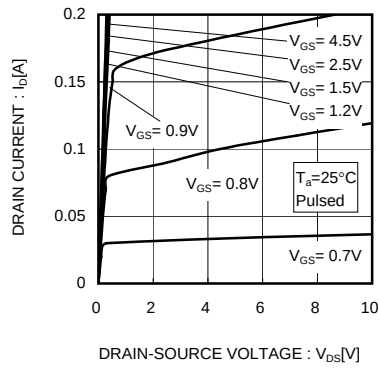


Fig.2 Typical Output Characteristics(II)

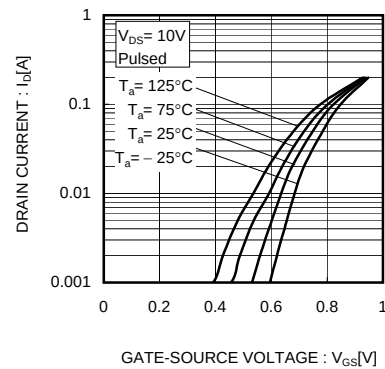


Fig.3 Typical Transfer Characteristics

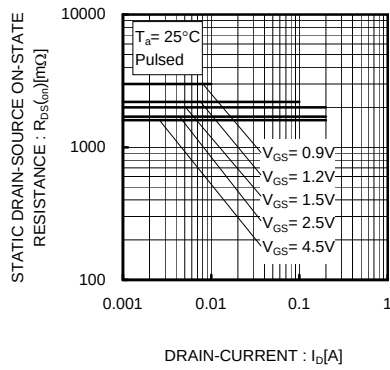


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

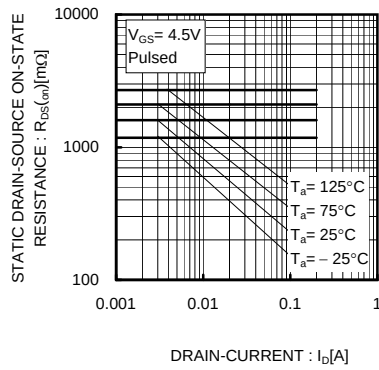


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

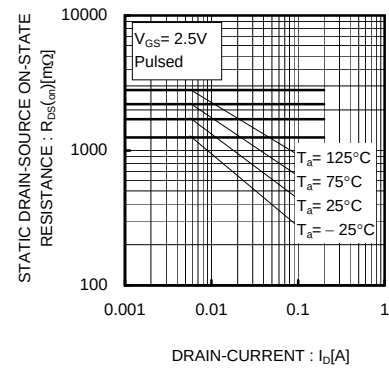


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

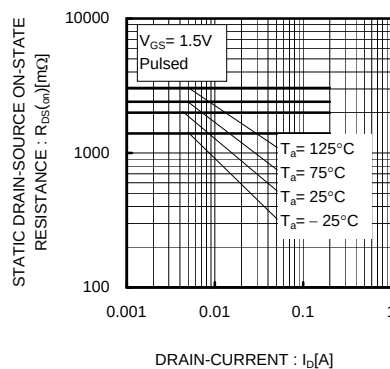


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

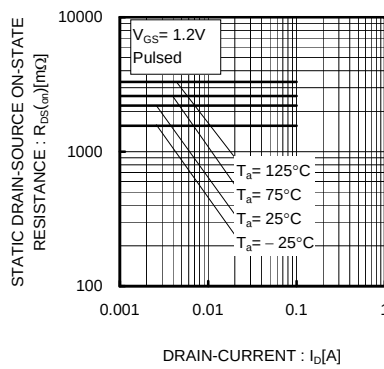


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(V)

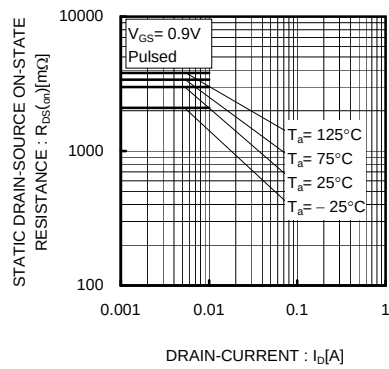


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current(VI)

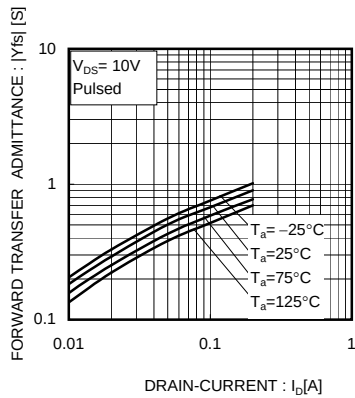


Fig.10 Forward Transfer Admittance vs. Drain Current

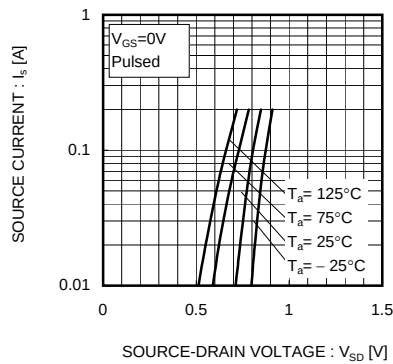


Fig.11 Reverse Drain Current vs. Source-Drain Voltage

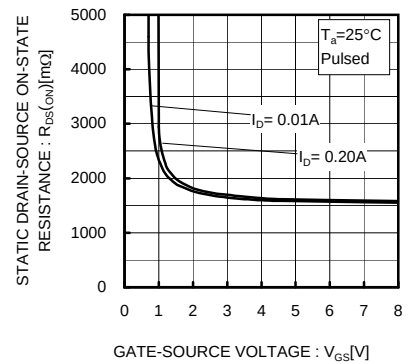


Fig.12 Static Drain-Source On-State Resistance vs. Gate Source Voltage

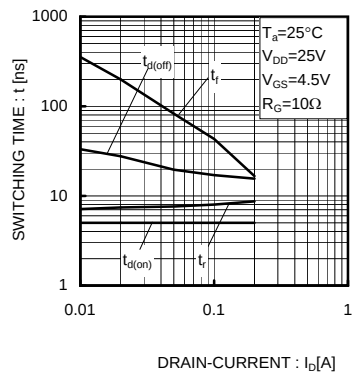


Fig.13 Switching Characteristics

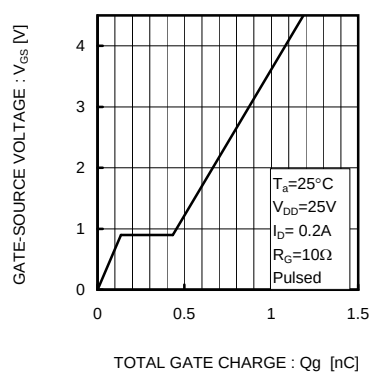


Fig.14 Typical Capacitance vs. Drain-Source Voltage

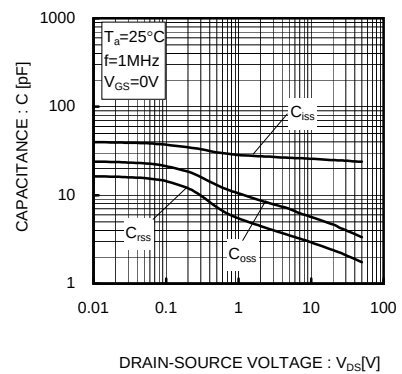


Fig.15 Typical Capacitance vs. Drain-Source Voltage

● Measurement circuits

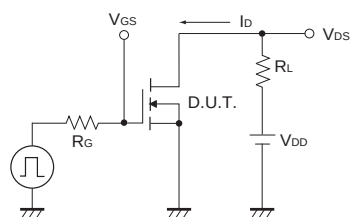


Fig.1-1 Switching time measurement circuit

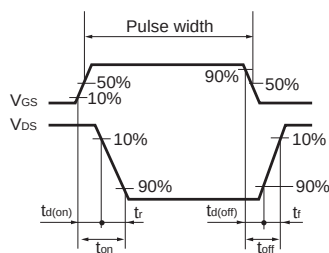


Fig.1-2 Switching waveforms

● Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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